

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

CLASSIFICATION ORDER 1872

DATE November 06, 2007

PROJECT NO. E 6508

The following classification changes will be effected by this order:

	<u>Class</u>	<u>Subclass</u>	<u>Art Unit</u>	<u>Ex'r Search Room No.</u>
Abolished:	365	49, 189.01, 210, 233	2827	0S001
Established:	365	49.1, 49.11-49.13, 49.15-49.18, 189.011, 189.14-189.19, 189.2, 210.1, 210.11-210.15, 233.1, 233.11-233.19	2827	0S001
Indent Changes:	365	207, 208, 209		
Title Changes:	365	50		

The following classes are also impacted by this order:

307, 327, 345, 359, 361, 369, 370, 375, 711

A. CLASSIFICATION MANUAL CHANGES

B. LISTING OF PRINCIPAL SOURCE OF ESTABLISHED
AND DISPOSITION OF ABOLISHED PAGES

C. CHANGES TO THE U.S.-I.P.C. CONCORDANCE

D. DEFINITION CHANGES AND NEW OR ADDITIONAL DEFINITIONS

CLASSIFICATION ORDER 1872
NOVEMBER 06, 2007
PROJECT NO. E-6508

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Publication Specialist: Yvonne Smith

NOVEMBER 2007

1	MAGNETIC BUBBLES	185.18	.Particular biasing
2	.Disposition of elements	185.19	..Multiple pulses (e.g., ramp)
3	..Lattice	185.2	..Reference signal (e.g., dummy cell)
4	.Decoder	185.21	...Sensing circuitry (e.g., current mirror)
5	.Logic		..Verify signal
6	.Rotating field circuits	185.22	..Drive circuitry (e.g., word line driver)
7	.Detectors	185.23	..Threshold setting (e.g., conditioning)
8	..Magnetoresistive	185.24	..Line charging (e.g., precharge, discharge, refresh)
9	..Hall effect	185.25	..Floating electrode (e.g., source, control gate, drain)
10	..Optical		..substrate bias
11	.Generators	185.26	..Tunnel programming
12	..By splitting		..Erase
13	.Plural interacting paths	185.27	...Over erasure
14	..Closed loop	185.28	...Nonsubstrate discharge
15	..Major-minor	185.29Radiation erasure
16	..With switch at interacting point	185.3	...Flash
17	..Idler switch	185.31	ANALOG STORAGE SYSTEMS
18	..Boundary	185.32	.Resistive
19	.Conductor propagation	185.33	.Thermoplastic
20	..Including A.C. signal	45	.Magnetic
21	..Three phase signals	46	* 49.1 ASSOCIATIVE MEMORIES (Content Addressable Memory-CAM)
22	.One's and zero's	47	.Flip-Flop
23	.Plural direction propagation	48	* 49.12 .Capacitor cell
24	..Nonsequential	* 49.1	* 49.13 .Ferroelectric cell
25	.Velocity		# 50 .Magnetic cell
26	..Turns	* 49.11	* 49.15 .Auxiliary lines
27	.Bias	* 49.12	* 49.16 .Segmented/Partitioned of cells
28	..Variable	* 49.13	* 49.17 .Compare/Search/Match circuit
29	.Strip domain	# 50	* 49.18 .Priority encoders
30	.In-plane field (nonrotating)	* 49.15	51 FORMAT OR DISPOSITION OF ELEMENTS
31	.Different size bubbles	* 49.16	52 HARDWARE FOR STORAGE ELEMENTS
32	.Multiple magnetic layer	* 49.17	53 .Shields
33	.Magnetic storage material	* 49.18	54 .Ground plane
34	..Amorphous	51	55 .Magnetic
35	.Guide structure	52	56 ..spacers
36	..Ion implantation	53	57 ..Keeper
37	..Slots or rails	54	58 ..Slot
38	..Zigzag	55	59 ..Embedded conductor
39	..Overlays	56	60 ..Air gap
40	...On opposite sides of storage medium	57	61 ..Hairpin conductor
41	...Dots	58	62 ..Permanent magnet
42	...Wedges	59	63 INTERCONNECTION ARRANGEMENTS
43	...Chevrons	60	64 .Optical
44	...Rectangular bars	61	65 .Ferroelectric
185.01	FLOATING GATE	62	66 .Magnetic
185.02	.Disturbance control	63	67 ..Plural diagonal
185.03	.Multiple values (e.g., analog)	64	68 ..Tree
185.04	.Data security	65	69 ..Crossover
185.05	.Particular connection	66	70 ..Woven
185.06	..Segregated columns	67	71 .Negative resistance
185.07	..Cross-coupled cell	68	72 .Transistors or diodes
185.08	..With volatile signal storage device	69	73 RECIRCULATION STORES
185.09	..Error correction (e.g., redundancy, endurance)	70	74 .Magnetic
185.1	..Extended floating gate	71	75 .Stepwise
185.11	..Bank or block architecture	72	76 .Delay lines
185.12	...Parallel row lines (e.g., page mode)	73	77 .Plural paths
185.13	...Global word or bit lines	74	78 PLURAL SHIFT REGISTER MEMORY DEVICES
185.14	..Program gate	75	
185.15	...Weak inversion injection	76	
185.16	..Virtual ground	77	
185.17	..Logic connection (e.g., NAND string)	78	

Title Change
* Newly Established Subclass

@ Indent Change
& Position Change

80	MAGNETIC SHIFT REGISTERS	142	..Aperture with transverse axis
81	.Bidirectional	143	...Biax
82	.Two cells per bit	144	..Same size apertures
83	.SiPo/PiSo	145	.Ferroelectric
84	.Core in transfer loop	146	.Electrets
85	.Continuous	147	.Persistent internal polarization (PIP)
86	..Plated wire	148	.Resistive
87	.Thin film	149	.Capacitors
88	..Domain tip	150	..Inherent
89	.Logic	151	.Molecular or atomic
90	.Multiaperture cell	152	..Nuclear induction or spin echo
91	..Ladder	153	.Electrochemical
92	..With other type core	154	.Flip-flop (electrical)
93	.Including delay means	155	..Plural emitter or collector
94	READ ONLY SYSTEMS (I.E.. SEMIPERMANENT)	156	..Complementary
95	.With override (i.e., latent images)	157	.Magnetostrictive or piezoelectric
96	.Fusible	158	.Magnetoresistive
97	.Magnetic	159	.Negative resistance
98	..Random core	160	.Superconductive
99	..Random wiring	161	..Thin film
100	.Resistive	162	..Josephson
101	.Inductive	163	.Amorphous (electrical)
102	.Capacitative	164	.Electrical contacts
103	.Semiconductive	165	..Coherer
104	..Transistors	166	..Relay
105	..Diodes	167	.Simulating biological cells
106	RADIANT ENERGY	168	.Ternary
107	.Chemical fluids	169	.Gunn effect
108	.Liquid crystal	170	.Hall effect
109	.Photoconductive and ferroelectric	171	.Magnetic thin film
110	.Electroluminescent and photoconductive	172	..Isotropic
111	.Electroluminescent	173	..Multiple magnetic storage layers
112	.Photoconductive	174	.Semiconductive
113	.Amorphous	175	..Diodes
114	.Semiconductive	176	..silicon on sapphire (SOS)
115	..Diodes	177	..Bioplar and FET
116	.Plasma	178	..Ion implantation
117	.Ferroelectric	179	..Plural emitter or collector
118	.Electron beam	180	..Four layer devices
119	.Color centers	181	..Complementary conductivity
120	INFORMATION MASKING	182	..Insulated gate devices
121	.Polarization	183	...Charge coupled
122	..Maymeto-optical	184	...Variable threshold
123	.Bragg cells	186	..Single device per bit
124	.Diffraction	187	..Three devices per bit
125	..Holograms	188	..Four or more devices per bit
126	.Thermoplastic	* 189.011	READ/WRITE CIRCUIT
127	.Transparency	189.02	.Multiplexing
128	.Electron beams	189.03	.Plural use of terminal
129	SYSTEMS USING PARTICULAR ELEMENT	189.04	.Simultaneous operations (e.g., read/write)
130	.Three-dimensional magnetic array		
131	.Two magnetic cells per bit	* 189.14	.Common read and write circuit
132	.Different size cores	* 189.15	.Particular read circuit
133	.Cells of diverse coercivity	* 189.16	.Particular write circuit
134	.Continuous cells	* 189.17	.Data transfer circuit
135	..Elongated or bar-shaped cell	* 189.18	.Bidirectional bus
136	...Twisters	* 189.19	.Separate read and write bus
137	...Tubular	* 189.2	.Using different memory types
138	...Chain	189.05	.Having particular data buffer or latch
139	...Plated wire	189.06	.Including signal clamping
140	.Multiaperture cell	189.07	.Including signal comparison
141	..Aperture plate		

Title Change
* Newly Established Subclass

@ Indent Change
& Position Change

189.08	READ/WRITE CIRCUIT .Including specified plural element logic arrangement	230.07 230.08	..Including magnetic element ..Including particular address buffer or latch circuit arrangement
189.09	.Including reference or bias voltage generator	230.09	.Combined random and sequential addressing
189.11	.Including level shift or pull-up circuit	231	.Using selective matrix
189.12	.With shift register	232	..Magnetic
190	.For complementary information	* 233.1	.Sync/clocking
191	.Signals	* 233.11	..Plural clock signals
192	..Radio frequency	* 233.12	..External clock signal modification
193	..Strobe	* 233.13	..DDR (double data rate) memory
194	..Delay	* 233.14	..Initiating signal
195	..Inhibit	* 233.15	..standby signal
196	..Sense/inhibit	* 233.16	..Write mode signal only
197	..Microwave	* 233.17	..Read mode signal only
198	..Transmission	* 233.18	..Burst mode signal
199	..coincident A.C. signal with pulse	* 233.19	..Common read and write mode signal
200	.Bad bit	233.5	..Transition detection
201	.Testing	234	.Optical
202	.Complementing/balancing	235	..Page memories
203	.Precharge	236	.Counting
204	.Accelerating charge or discharge	237	.Electron beam
205	.Flip-flop used for sensing	238	.Cartesian memories
206	.Noise suppression	238.5	.Byte or page addressing
@ 207	.Differential sensing	239	.Sequential
@ 208	..Semiconductors	240	..Using shift register
@ 209	..Magnetic	241	..Detectors
* 210.1	..Reference or dummy element	242	.Current Steering
* 210.11	..Compensate signal	243	..Diode
* 210.12	..Voltage setting	243.5	..Including magnetic element
* 210.13	..Common bit line	244	MISCELLANEOUS
* 210.14	..Plural elements per reference cell		*****
* 210.15	..Structural component of a reference cell		FOREIGN ART COLLECTION

		FOR 000	CLASS-RELATED FOREIGN DOCUMENTS
211	..Temperature compensation		
212	..Semiconductor		
213	..Magnetic		
214	..Particular wiring		
215	.Optical		
216	..Holographic		
217	.Electron beam		
218	.Erase		
219	.SiPo/PiSo		
220	.Parallel read/write		
221	.Serial read/write		
222	.Data refresh		
223	.Bridge		
224	.Eddy current		
225	.Minor loop		
225.5	.Including magnetic element		
225.6	.Having bipolar circuit element		
225.7	.Having fuse element		
226	POWERING		
227	.Conservation of power		
228	.Data preservation		
229	..standby power		
230.01	ADDRESSING		
230.02	.Multiplexing		
230.03	.Plural blocks or hanks		
230.04	..Alternate addressing (e.g., even/odd)		
230.05	.Multiple port access		
230.06	.Particular decoder or driver circuit		

Title Change
* Newly Established Subclass

@ Indent Change
& Position Change

NOVEMBER 6, 2007

PROJECT E-6508

SOURCE CLASSIFICATION(S) OF PATENTS
IN NEWLY ESTABLISHED SUBCLASSES REPORT

generated by: Data Control Division

New Classification	Number Of ORs	Source Classification	Number Of ORs
-----	-----	-----	-----
257/206	1	365/189.01	469
327/175	1	365/233	1147
335/207	1	365/210	267
365/104	1	365/189.01	469
	1	365/210	267
365/120	1	365/189.01	469
365/145	1	365/210	267
	1	365/233	1147
365/148	1	365/210	267
365/149	14	365/210	267
	2	365/233	1147
365/154	9	365/233	1147
365/158	1	365/189.01	469
	4	365/210	267
	1	365/233	1147
365/171	2	365/210	267
365/174	1	365/210	267
365/175	1	365/210	267
365/185.01	1	365/189.01	469
	1	365/210	267
365/185.05	1	365/233	1147
365/185.06	1	365/189.01	469
365/185.13	1	365/189.01	469
	1	365/210	267
365/185.14	1	365/189.01	469
365/185.17	15	365/233	1147
365/185.18	1	365/189.01	469
365/185.2	5	365/210	267
365/185.21	1	365/210	267
	1	365/233	1147
365/185.23	1	365/189.01	469
365/185.24	1	365/210	267
365/185.26	1	365/210	267
365/185.28	1	365/233	1147
365/185.29	1	365/233	1147
365/185.33	1	365/210	267
365/189.011	28	365/189.01	469
	1	365/210	267
	4	365/233	1147
365/189.02	5	365/189.01	469
	1	365/210	267

SOURCE CLASSIFICATION(S) OF PATENTS
IN NEWLY ESTABLISHED SUBCLASSES REPORT

NOVEMBER 6, 2007

PROJECT E-6508

Generated by: Data Control Division

New Classification -----	Number Of ORs -----	Source Classification -----	Number Of ORs -----
	16	365/233	1147
365/189.03	18	365/189.01	469
	1	365/210	267
365/189.03	3	365/233	1147
365/189.04	12	365/189.01	469
	2	365/233	1147
365/189.05	3	365/189.01	469
	1	365/210	267
	22	365/233	1147
365/189.06	1	365/49	789
365/189.07	6	365/189.01	469
	5	365/210	267
	10	365/233	1147
365/189.08	1	365/189.01	469
	1	365/210	267
	5	365/233	1147
365/189.09	4	365/189.01	469
	8	365/210	267
	4	365/233	1147
365/189.11	2	365/189.01	469
	1	365/210	267
365/189.12	1	365/210	267
365/189.14	77	365/189.01	469
	1	365/210	267
	29	365/233	1147
365/189.15	128	365/189.01	469
	9	365/210	267
	49	365/233	1147
365/189.16	99	365/189.01	469
	1	365/210	267
	17	365/233	1147
365/189.17	13	365/189.01	469
	7	365/233	1147
365/189.18	19	365/189.01	469
	3	365/233	1147
365/189.19	6	365/189.01	469
	1	365/233	1147
365/189.2	3	365/189.01	469
	1	365/233	1147
365/190	1	365/189.01	469

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SOURCE CLASSIFICATION(S) OF PATENTS
IN NEWLY ESTABLISHED SUBCLASSES REPORT

Generated by: Data Control Division

New Classification	Number Of ORs	Source Classification	Number Of ORs
	6	365/210	267
365/191	1	365/210	267
	5	365/233	1147
365/193	10	365/233	1147
365/194	1	365/210	267
	32	365/233	1147
365/195	1	365/189.01	469
365/195	1	365/233	1147
365/196	1	365/189.01	469
365/200	2	365/189.01	469
	1	365/210	267
365/201	3	365/189.01	469
	1	365/210	267
	1	365/233	1147
365/203	1	365/189.01	469
	5	365/210	267
	1	365/233	1147
365/205	2	365/189.01	469
	12	365/210	267
365/207	2	365/189.01	469
	17	365/210	267
365/208	1	365/233	1147
365/210.1	91	365/210	267
	2	365/233	1147
365/210.11	2	365/210	267
	1	365/233	1147
365/210.12	34	365/210	267
365/210.13	1	365/189.01	469
	8	365/210	267
365/210.14	1	365/189.01	469
	3	365/210	267
365/210.15	7	365/210	267
365/218	1	365/233	1147
365/221	1	365/189.01	469
	1	365/233	1147
365/222	1	365/233	1147
365/225.7	1	365/210	267
365/226	1	365/189.01	469
	1	365/233	1147

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PROJECT E-6508

SOURCE CLASSIFICATION(S) OF PATENTS
IN NEWLY ESTABLISHED SUBCLASSES REPORT

Generated by: Data Control Division

New Classification	Number Of ORs	Source Classification	Number Of ORs
365/227	1	365/233	1147
365/230.01	8	365/233	1147
	1	365/49	789
365/230.02	4	365/233	1147
365/230.03	1	365/189.01	469
	20	365/233	1147
365/230.04	2	365/189.01	469
	4	365/233	1147
365/230.06	6	365/189.01	469
	4	365/210	267
	11	365/233	1147
365/230.08	1	365/189.01	469
365/230.08	2	365/233	1147
365/230.09	1	365/189.01	469
	2	365/233	1147
365/233.1	1	365/189.01	469
	392	365/233	1147
365/233.11	1	365/189.01	469
	105	365/233	1147
365/233.12	74	365/233	1147
365/233.13	39	365/233	1147
365/233.14	83	365/233	1147
365/233.15	1	365/189.01	469
	10	365/233	1147
365/233.16	54	365/233	1147
365/233.17	37	365/233	1147
365/233.18	2	365/189.01	469
	14	365/233	1147
365/233.19	9	365/233	1147
365/233.5	3	365/233	1147
365/236	1	365/233	1147
365/45	1	365/49	789
365/49.1	1	365/210	267
	214	365/49	789
365/49.11	74	365/49	789
365/49.12	31	365/49	789
365/49.13	4	365/49	789
365/49.15	109	365/49	789

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SOURCE CLASSIFICATION (S) OF PAGES
IN NEWLY ESTABLISHED SUBCLASSES REPORT

Generated by: Data Control Division

New Classification	Number Of ORs	Source Classification	Number Of ORs
365/49.16	24	365/49	789
365/49.17	271	365/49	789
365/49.18	45	365/49	789
365/50	2	365/49	789
365/51	1	365/210	267
	4	365/233	1147
365/63	1	365/210	267
	3	365/233	1147
	1	365/49	789
365/94	1	365/189.01	469
	1	365/210	267
	2	365/233	1147
711/102	1	365/210	267
711/105	4	365/49	789
711/108	6	365/49	789
711/125	1	365/49	789
711/167	1	365/233	1147
712/208	1	365/189.01	469

CLASSIFICATION ORDER 1872
NOVEMBER 6, 2007

B-1

PROJECT E-6508

DISPOSITION CLASSIFICATION(S) OF PATENTS
FROM ABOLISHED SUBCLASSES REPORT

Generated by: Data Control Division

Source Classification	Number Of ORs	New Classification	Number Of ORs
365/189.01	469	257/206	1
		365/104	1
		365/120	1
		365/158	1
		365/185.01	1
		365/185.06	1
		365/185.13	1
		365/185.14	1
		365/185.18	1
		365/185.23	1
		365/189.011	28
		365/189.02	5
		365/189.03	18
		365/189.04	12
		365/189.05	3
		365/189.07	6
		365/189.08	1
		365/189.09	4
		365/189.11	2
		365/189.14	77
		365/189.15	128
		365/189.16	99
		365/189.17	13
		365/189.18	19
		365/189.19	6
		365/189.2	3
		365/190	1
		365/195	1
		365/196	1
		365/200	2
		365/201	3
		365/203	1
		365/205	2
		365/207	2
		365/210.13	1
		365/210.14	1
		365/221	1
		365/226	1
		365/230.03	1
		365/230.04	2
		365/230.06	6

CLASSIFICATION ORDER 1872
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B-2

PROJECT E-6508

DISPOSITION CLASSIFICATION(S) OF PATENTS
 FROM ABOLISHED SUBCLASSES REPORT

Generated by: Data Control Division

Source Classification	Number Of ORs	New Classification	Number Of ORs
365/230.08	1	365/230.09	1
		365/233.1	1
		365/233.11	1
		365/233.15	1
365/189.01	469	365/233.18	2
		365/94	1
		712/208	1
365/210	267	335/207	1
		365/104	1
		365/145	1
		365/148	1
		365/149	14
		365/158	4
		365/171	2
		365/174	1
		365/175	1
		365/185.01	1
		365/185.13	1
		365/185.2	5
		365/185.21	1
		365/185.24	1
		365/185.26	1
		365/185.33	1
		365/189.011	1
		365/189.02	1
		365/189.03	1
		365/189.05	1
		365/189.07	5
		365/189.08	1
		365/189.09	8
		365/189.11	1
		365/189.12	1
		365/189.14	1
		365/189.15	9
		365/189.16	1
		365/190	6
		365/191	1
		365/194	1

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DISPOSITION CLASSIFICATION(S) OF PATENTS
 FROM ABOLISHED SUBCLASSES REPORT

Generated by: Data Control Division

Source Classification	Number Of ORs	New Classification	Number Of ORs
		365/200	1
		365/201	1
		365/203	5
		365/205	12
		365/207	17
		365/210.1	91
		365/210.11	2
		365/210.12	34
		365/210.13	8
		365/210.14	3
		365/210.15	7
		365/225.7	1
365/210	267	365/230.06	4
		365/49.1	1
		365/51	1
		365/63	1
		365/94	1
		711/102	1
365/233	1147	327/175	1
		365/145	1
		365/149	2
		365/154	9
		365/158	1
		365/185.05	1
		365/185.17	15
		365/185.21	1
		365/185.28	1
		365/185.29	1
		365/189.011	4
		365/189.02	16
		365/189.03	3
		365/189.04	2
		365/189.05	22
		365/189.07	10
		365/189.08	5
		365/189.09	4
		365/189.14	29
		365/189.15	49
		365/189.16	17

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DISPOSITION CLASSIFICATION(S) OF PATENTS
FROM ABOLISHED SUBCLASSES REPORT
PROJECT: E6508

Generated by: Data Control Division

Source Classification	Number Of ORs	New Classification	Number Of ORs
		365/189.17	7
		365/189.18	3
		365/189.19	1
		365/189.2	1
		365/191	5
		365/193	10
		365/194	32
		365/195	1
		365/201	1
		365/203	1
		365/208	1
		365/210.1	2
		365/210.11	1
		365/218	1
		365/221	1
		365/222	1
		365/226	1
		365/227	1
		365/230.01	8
365/233	1147	365/230.02	4
		365/230.03	20
		365/230.04	4
		365/230.06	11
		365/230.08	2
		365/230.09	2
		365/233.1	392
		365/233.11	105
		365/233.12	74
		365/233.13	39
		365/233.14	83
		365/233.15	10
		365/233.16	54
		365/233.17	37
		365/233.18	14
		365/233.19	9
		365/233.5	3
		365/236	1
		365/51	4
		365/63	3
		365/94	2

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DISPOSITION CLASSIFICATION(S) OF PATENTS
FROM ABOLISHED SUBCLASSES REPORT
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Generated by: Data Control Division

Source	Number	New	Number
365/49	789	365/189.06	1
		365/230.01	1
		365/45	1
		365/49.1	214
		365/49.11	74
		365/49.12	31
		365/49.13	4
		365/49.15	109
		365/49.16	24
		365/49.17	271
		365/49.18	45
		365/50	2
		365/63	1
		711/105	4
		711/108	6
		711/125	1

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C. CHANGES TO THE USPC-TO-IPC CONCORDANCE

<u>Class</u>	<u>USPC</u> Subclass	<u>IPC</u> Subclass	<u>Notation</u>
365	49.1	G11C	15/00
	49.11	G11C	15/00
	49.12	G11C	15/04
	49.13	G11C	15/00
	50	G11C	15/02
	49.15	G11C	15/00
	49.16	G11C	15/00
	49.17	G11C	15/00
	49.18	G11C	15/00
	189.011	G11C	7/00, 7/22
	189.02	G11C	7/00
	189.03	G11C	7/10
	189.04	G11C	7/00, 7/22
	189.14	G11C	7/00, 7/22
	189.15	G11C	7/00, 7/22
	189.16	G11C	7/00, 7/22
	189.17	G11C	7/10
	189.18	G11C	7/18, 7/00
	189.19	G11C	7/18, 7/00
	189.2	G11C	7/00
	210.1	G11C	7/02
	210.11	G11C	7/02
	210.12	G11C	7/02
	210.13	G11C	7/02
	210.14	G11C	7/02
	210.15	G11C	7/02
	233.1	G11C	8/00
	233.11	G11C	8/18
	233.12	G11C	8/18
	233.13	G11C	8/16
	233.14	G11C	8/00; 8/18
	233.15	G11C	8/00; 8/18
	233.16	G11C	8/00; 8/18
	233.17	G11C	8/00; 8/18
	233.18	G11C	8/00; 8/18
	233.19	G11C	8/00; 8/18

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D. CHANGES TO THE DEFINITIONS

CLASS 307 – ELECTRICAL TRANSMISSION OR INTERCONNECTION SYSTEMS

Class Definition: Section II, under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclasses 185.01+ for floating gate memory storage (e.g., flash memory), subclass 73 for recirculation of information in a storage read/write system, subclass 78 for plural shift register memory devices, subclass 80 for magnetic shift register, per se, subclasses 129+ for storage systems using a particular storage element, subclasses 189.01+ for read/write circuits peculiar to a storage and retrieval system, and subclass 230 for addressing circuits peculiar to a storage and retrieval system.

Insert:

365, Static Information Storage and Retrieval, subclasses 185.01+ for floating gate memory storage (e.g., flash memory), subclass 73 for recirculation of information in a storage read/write system, subclass 78 for plural shift register memory devices, subclass 80 for magnetic shift register, per se, subclasses 129+ for storage systems using a particular storage element, subclass 189.011 for read/write circuits peculiar to a storage and retrieval system, and subclass 230 for addressing circuits peculiar to a storage and retrieval system.

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D. CHANGES TO THE DEFINITIONSCLASS 327 – MISCELLANEOUS ACTIVE ELECTRICAL NONLINEAR DEVICES,
CIRCUITS, AND SYSTEMS

Class Definition: Section IV, under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclasses 73+ for recirculation of information in a storage read/write system, subclass 78 for plural shift register memory devices, subclasses 80+ for magnetic shift register, per se, subclasses 129+ for storage systems using a particular storage element, subclasses 189.01+ for read/write circuits peculiar to a storage and retrieval system, and subclasses 230.01+ for addressing circuits peculiar to a storage and retrieval system. (Also see "Charge Coupled Devices" above).

Insert:

365, Static Information Storage and Retrieval, subclasses 73+ for recirculation of information in a storage read/write system, subclass 78 for plural shift register memory devices, subclasses 80+ for magnetic shift register, per se, subclasses 129+ for storage systems using a particular storage element, subclass 189.011 for read/write circuits peculiar to a storage and retrieval system, and subclasses 230.01+ for addressing circuits peculiar to a storage and retrieval system. (Also see "Charge Coupled Devices" above).

Subclass 51: Under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclasses 189.01+ for networks including the inserting, extracting, or handling of information signals using the functions of "write", "read-out", "erase", etc., subclasses 185.01+ for floating gate memory storage (e.g., flash memory); subclasses 189.01+ for the static storage and retrieval of information coupled with the functions of "write", "read-out", "erase", etc., wherein voltage amplitude is sensed.

Insert:

365, Static Information Storage and Retrieval, subclasses 207- 210.15 for the static storage and retrieval of information coupled with the

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functions of "write", "read-out", "erase", etc., wherein voltage amplitude is sensed.

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CLASS 345 – COMPUTER GRAPHICS PROCESSING AND SELECTIVE VISUAL DISPLAY SYSTEMS

Subclass 519: Under SEE OR SEARCH CLASS

Delete:

- 365, Static Information Storage and Retrieval, appropriate subclasses, in particular subclasses 189.01+ and 230.01+ for read/write and addressing circuitry for a semiconductor structure device

Insert:

- 365, Static Information Storage and Retrieval, appropriate subclasses, in particular subclasses 189.011 and 230.01+ for read/write and addressing circuitry for a semiconductor structure device.

Subclass 530: Under SEE OR SEARCH CLASS

Delete:

- 365, Static Information Storage and Retrieval, various subclasses for static memory devices including internal elements of the memory, particularly subclasses 189.01 through 189.12 for read/write circuits and subclasses 230.01-230.09 for addressing of addressable, static single storage elements or plural elements; subclass 189.05 for buffering or latching data being read from or written to memory; subclass 189.08 for logic devices in combination with memory systems; subclasses 200 and 201 for testing of memory systems; and subclass 230.08 for buffering and latching address data being employed to access memory.

Insert:

- 365, Static Information Storage and Retrieval, various subclasses for static memory devices including internal elements of the memory, particularly subclasses 189.011 through 189.19 for read/write circuits and subclasses 230.01-230.09 for addressing of addressable, static single storage elements or plural elements; subclass 189.05 for buffering or latching data being read from or written to memory; subclass 189.08 for logic devices in combination with memory systems; subclasses 200 and 201 for testing of memory systems; and subclass 230.08 for buffering and latching address data being employed to access memory.

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Subclass 531: Under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclasses, 189.01-189.12 for read/write circuit.

Insert

365, Static Information Storage and Retrieval, subclasses, 189.01 through 189.19 for read/write circuit.

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D. CHANGES TO THE DEFINITIONS

CLASS 359 – OPTICAL: SYSTEMS AND ELEMENTS

Subclass 11: Under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclass 49 for associative holographic memories.

Insert:

365, Static Information Storage and Retrieval, subclass 49.1 for associative holographic memories.

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D. CHANGES TO THE DEFINITIONS

CLASS 361 – ELECTRICITY: ELECTRICAL SYSTEMS AND DEVICES

Subclass 684: Under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclasses 1+ for magnetic bubbles, per se; subclasses 185.01+ for floating gate memory storage (e.g., flash memory); subclasses 45+ for analog storage systems, per se; subclasses 49+ for associative memories, per se; and subclasses 94+ for read only systems, per se.

Insert:

365, Static Information Storage and Retrieval, subclasses 1+ for magnetic bubbles, per se; subclasses 185.01+ for floating gate memory storage (e.g., flash memory); subclasses 45+ for analog storage systems, per se; subclasses 49.1 through 50 for associative memories, per se; and subclasses 94+ for read only systems, per se.

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D. CHANGES TO THE DEFINITIONS

CLASS 365 – STATIC INFORMATION STORAGE AND RETRIEVAL

Definitions AbolishedSubclasses

49, 189.01, 210, 233

Definitions Modified

Class Definition: Section III, under SEE OR SEARCH THIS CLASS, SUBCLASS

Delete:

49, through 243.5, digital storage systems, for devices where the information is discrete.

Insert:

49.1, through 243.5, digital storage systems, for devices where the information is discrete.

Subclass 50: In the subclass definition

Delete:

50 This subclass is indented under subclass 49. Subject matter where the associative memories storage elements are magnetic.

Insert:**50 Magnetic cell:**
Subject matter under subclass 49.1 wherein the storage element changes a storage state when a magnetic field is applied.

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Subclass 63: Under SEE OR SEARCH THIS CLASS, SUBCLASS

Delete:

189.01+, for reading or writing information from or into a static memory device.

Insert:

189.011, for reading or writing information from or into a static memory device

Subclass 185.2: Under SEE OR SEARCH THIS CLASS, SUBCLASS

Delete:

210, for noise suppression by differential sensing using a reference or dummy elements.

Insert:

210.1, for noise suppression by differential sensing using a reference or dummy elements.

Subclass 189.02: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter which includes the transmission of plural signals over a single signal path.

Insert:

This subclass is indented under subclass 189.011. Subject matter which includes the transmission of plural signals over a single signal path.

Subclass 189.03: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter which has a terminal connecting the memory to a data handling circuit and another diverse circuit.

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This subclass is indented under subclass 189.011. Subject matter which has a terminal connecting the memory to a data handling circuit and another diverse circuit.

Subclass 189.04: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter including circuitry for performing multiple operations (e.g., storing information in and retrieving information from the memory) at the same time.

Insert:

This subclass is indented under subclass 189.011. Subject matter including circuitry for performing multiple operations (e.g., storing information in and retrieving information from the memory) at the same time.

Subclass 189.05: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter including a specific detail of a temporary storage circuit for a data signal.

Insert:

This subclass is indented under subclass 189.011. Subject matter including a specific detail of a temporary storage circuit for a data signal.

Subclass 189.06: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter including circuitry for limiting the variation of a signal (e.g., voltage) in order to keep such variation at a predetermined level.

Insert:

This subclass is indented under subclass 189.011. Subject matter including circuitry for limiting the variation of a signal (e.g., voltage) in order to keep such variation at a predetermined level.

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Subclass 189.07: In the subclass definition

Delete :

This subclass is indented under subclass 189.01. Subject matter including circuitry to compare plural signal in order to control an operation of the system on a data signal.

Insert:

This subclass is indented under subclass 189.011. Subject matter including circuitry to compare plural signal in order to control an operation of the system on a data signal.

Under SEE OR SEARCH THIS CLASS, SUBCLASS

Delete:

49, for a comparator in a content addressable memory.

Insert:

49.17, for a comparator in a content addressable memory.

Subclass 189.08: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter describing the configuration of multiple logic devices which handle the information signal.

Insert:

This subclass is indented under subclass 189.011. Subject matter describing the configuration of multiple logic devices which handle the information signal.

Subclass 189.09: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter including a particular voltage or bias source.

Insert:

This subclass is indented under subclass 189.011. Subject matter including a particular voltage or bias source.

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D. CHANGES TO THE DEFINITIONS

Under SEE OR SEARCH THIS CLASS, SUBCLASS

Delete:

210, for an element used to generate reference voltage for a sense amplifier.

Insert:

210.1-210.15, for an element used to generate reference voltage for a sense amplifier.

Subclass 189.11 : In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter including a circuit element which makes an adjustment in the voltage level of an information signal to enhance driving capability.

Insert:

This subclass is indented under subclass 189.011. Subject matter including a circuit element which makes an adjustment in the voltage level of an information signal to enhance driving capability.

Subclass 189.12: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter including a circuit which sequentially shifts the data information signal between one element and another in a memory array in a serial manner.

Insert:

This subclass is indented under subclass 189.011. Subject matter including a circuit which sequentially shifts the data information signal between one element and another in a memory array in a serial manner.

Subclass 190: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter wherein the read/write circuit is used with a memory cell containing complementary information.

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This subclass is indented under subclass 189.011. Subject matter wherein the read/write circuit is used with a memory cell containing complementary information.

Subclass 191: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter where particular signals are used for writing, maintaining, or reading information.

Insert:

This subclass is indented under subclass 189.011. Subject matter where particular signals are used for writing, maintaining, or reading information.

Subclass 200: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter in which erroneous, defective, or partially defective storage locations are used to store information.

Insert:

This subclass is indented under subclass 189.011. Subject matter in which erroneous, defective, or partially defective storage locations are used to store information.

Subclass 201: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter including the specifics of the memory which are tested for defects or erroneous information.

Insert:

This subclass is indented under subclass 189.011. Subject matter including the specifics of the memory which are tested for defects or erroneous information.

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Subclass 202: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter in which complementing or balancing signals are used in a read/write circuit, e.g., a storage system having an auxiliary storage circuit for complementary signals to be used for noise cancellation.

Insert:

This subclass is indented under subclass 189.011. Subject matter in which complementing or balancing signals are used in a read/write circuit, e.g., a storage system having an auxiliary storage circuit for complementary signals to be used for noise cancellation.

Subclass 203: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter wherein circuit lines or elements are charged (or discharged) to a desired level just prior to reading or writing information.

Insert:

This subclass is indented under subclass 189.011. Subject matter wherein circuit lines or elements are charged (or discharged) to a desired level just prior to reading or writing information.

Subclass 204: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter wherein a circuit senses a charging (or discharging) operation and switches in a parallel path to decrease the charging (or discharging) time.

Insert:

This subclass is indented under subclass 189.011. Subject matter wherein a circuit senses a charging (or discharging) operation and switches in a parallel path to decrease the charging (or discharging) time.

Subclass 205 : In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter wherein the sensing circuit is a flip-flop circuit.

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This subclass is indented under subclass 189.011. Subject matter wherein the sensing circuit is a flip-flop circuit.

Subclass 206: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter having circuits for cancellation or reduction of noise or spurious signals.

Insert:

This subclass is indented under subclass 189.011. Subject matter having circuits for cancellation or reduction of noise or spurious signals.

Subclass 207: In the subclass definition

Delete:

This subclass is indented under subclass 206. Subject matter where the circuit used is of the differential sensing type.

Insert:

This subclass is indented under subclass 189.011. Subject matter includes a circuit for detecting the difference between two voltage or current levels.

Subclass 215: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter in which the read/write circuit is for an optical storage system.

Insert:

This subclass is indented under subclass 189.011. Subject matter in which the read/write circuit is for an optical storage system.

Subclass 217: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter in which the read/write circuit is for an electron beam storage system.

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This subclass is indented under subclass 189.011. Subject matter in which the read/write circuit is for an electron beam storage system.

Subclass 218: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter in which the read/write circuit is or includes an erase circuit for a storage system.

Insert:

This subclass is indented under subclass 189.011. Subject matter in which the read/write circuit is or includes an erase circuit for a storage system.

Subclass 219: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter in which the read/write circuit for memory provides Serial Input with Parallel Output or Parallel Input with Serial Output.

Insert:

This subclass is indented under subclass 189.011. Subject matter in which the read/write circuit for memory provides Serial Input with Parallel Output or Parallel Input with Serial Output.

Subclass 220: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter wherein information is written into a memory in parallel form and read out in parallel form.

Insert:

This subclass is indented under subclass 189.011. Subject matter wherein information is written into a memory in parallel form and read out in parallel form.

Subclass 221: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter wherein information is written into a memory in serial form and read out in serial form.

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D. CHANGES TO THE DEFINITIONSInsert:

This subclass is indented under subclass 189.011. Subject matter wherein information is written into a memory in serial form and read out in serial form.

Subclass 222 : In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter wherein decaying information is read before it becomes unrecognizable, and rewritten in original form, e.g., charge on a capacitor is read before too much has leaked off, then rewritten to a fully charged state.

Insert:

This subclass is indented under subclass 189.011. Subject matter wherein decaying information is read before it becomes unrecognizable, and rewritten in original form, e.g., charge on a capacitor is read before too much has leaked off, then rewritten to a fully charged state.

Subclass 223 : In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter where the sensing circuit is in the form of a bridge circuit.

Insert:

This subclass is indented under subclass 189.011. Subject matter where the sensing circuit is in the form of a bridge circuit.

Subclass 224: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter having circuits containing Eddy currents.

Insert:

This subclass is indented under subclass 189.011. Subject matter having circuits containing Eddy currents.

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Subclass 225: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter where the read/write circuit results in the operation of a magnetic memory element or any hysteresis loop other than the major loop.

Insert:

This subclass is indented under subclass 189.011. Subject matter where the read/write circuit results in the operation of a magnetic memory element or any hysteresis loop other than the major loop.

Subclass 225.5: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter including a semiconductor element having plural potential barriers (i.e., junctions).

Insert:

This subclass is indented under subclass 189.011. Subject matter including a semiconductor element having plural potential barriers (i.e., junctions).

Subclass 225.6: In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter including a semiconductor element having plural potential barriers (i.e., junctions).

Insert:

This subclass is indented under subclass 189.011. Subject matter including a semiconductor element having plural potential barriers (i.e., junctions).

Subclass 225.7 : In the subclass definition

Delete:

This subclass is indented under subclass 189.01. Subject matter wherein the circuit includes a circuit element which is selectively melted or disintegrated to make or break an electric circuit to control the operating characteristics of a memory read or write circuit.

Insert:

This subclass is indented under subclass 189.011. Subject matter wherein the circuit includes a circuit element which is selectively melted or disintegrated to

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make or break an electric circuit to control the operating characteristics of a memory read or write circuit.

Subclass 230.01: Under SEE OR SEARCH THIS CLASS, SUBCLASS

Delete:

189.01+, for the reading or writing of information in a memory system.

Insert:

189.011, for the reading or writing of information in a memory system.

Subclass 233.5: In the subclass definition

Delete:

This subclass is indented under subclass 233. Subject matter which generates a clock or timing signal responsive to a change in an input signal.

Insert:

This subclass is indented under subclass 233.1. Subject matter which generates a clock or timing signal responsive to a change in an input signal.

Definition established**49.1 ASSOCIATIVE MEMORIES (Content Addressable Memory-CAM)**

This subclass is indented under the class definition. Subject matter wherein the location of the information is determined by its content rather than by its address.

(1) Note. associative memories are also referred to as content or tag memories.

49.11 Flip-Flop:

Subject matter under subclass 49.1 wherein the storage element is a bistable logic circuit (i.e., one in which information need not be periodically refreshed).

49.12 Capacitor cell:

Subject matter under subclass 49.1 wherein the storage element is a capacitive device (i.e., one in which information need to be periodically refreshed).

49.13 Ferroelectric cell:

Subject matter under subclass 49.1 wherein the storage element is a ferroelectric memory cell.

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D. CHANGES TO THE DEFINITIONS**49.15 Auxiliary lines:**

Subject matter under subclass 49.1 where a line that carries hit/miss signals (match or mismatch signals) in a content addressable memory (CAM) is used for comparison in addition to the lines that carry the bit lines.

49.16 Segmented/Partitioned of cells:

Subject matter under subclass 49.1 where CAM elements are grouped into segments or partitions.

49.17 Compare/Search/Match circuit:

Subject matter under subclass 49.1 including a circuit for comparison of storage data and search data and outputting match/mismatch (hit/miss) signals.

49.18 Priority encoders:

Subject matter under subclass 49.1 including means to indicate an order of transmission of search data in a content addressable memory (CAM).

189.011 READ/WRITE CIRCUIT:

This subclass is indented under the class definition. Subject matter for inserting, extracting, or handling of an information signal to be stored (write circuit) or retrieved (read circuit).

189.14 Common read and write circuit:

Subject matter under subclass 189.011 including a circuit for controlling both reading and writing of data signal from/to a memory location.

189.15 Particular read circuit:

Subject matter under subclass 189.011 including a circuit for controlling reading of data signal from a memory location.

189.16 Particular write circuit:

Subject matter under subclass 89.011 including a circuit for controlling writing of data signal to a memory location.

189.17 Data transfer circuit:

Subject matter under subclass 189.011 including a circuit that connects between two storage locations (e.g., two memory arrays or memory blocks) for transferring data between them.

189.18 Bidirectional bus:

Subject matter under subclass 189.011 wherein data input/output lines are used for both reading and writing of data.

189.19 Separate read and write bus:

Subject matter under subclass 189.011 wherein each of read and write bus is unidirectional.

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- 189.2 Using different memory types:**
Subject matter under subclass 189.011 including a bus interface circuit between independent memory types (e.g., DRAM and SRAM).
- 210.1 Reference or dummy element:**
This subclass is indented under subclass 207. Subject matter including an additional cell that is used as a reference during the differential sensing.
- 210.11 Compensate signal:**
Subject matter under subclass 210.1 wherein the output signal from an additional (reference) circuit is used to offset undesired voltage variations.
- 210.12 Voltage setting:**
Subject matter under subclass 210.1 wherein a reference voltage is selected according to storage levels or operation modes.
- 210.13 Common bit line:**
Subject matter under subclass 210.1 wherein a reference cell shares the same bit/data line with a storage element.
- 210.14 Plural elements per reference cell:**
Subject matter under subclass 210.1 wherein a reference cell has more than one electronic components (e.g., containing a combination of transistors, capacitors, resistors, fuse, etc.).
- 210.15 Structural component of a reference cell:**
Subject matter under subclass 210.1 Including the structure of the electronic component (e.g., transistor, resistor, capacitor, fuse, etc.) that makes up a reference cell.
- 233.1 Sync/clocking**
This subclass is intended under subclass 230.01. Subject matter where a circuit that generates a clock signal for controlling a memory cell and/or a circuit that makes a clock cycle occurring in a predetermined time sequence or in phase, is used to select a memory location.
- 233.11 Plural clock signals:**
Subject matter under subclass 233.1 where there are two or more clock signals.
- 233.12 External clock signal modification:**
Subject matter under subclass 233.1 wherein an external clock signal is adjusted.
- 233.13 DDR (double data rate) memory:**
Subject matter under subclass 233.1 wherein a data memory reads or writes on a low to high transition of a clock signal and an opposite transition.

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D. CHANGES TO THE DEFINITIONS**233.14 Initiating signal:**

Subject matter under subclass 233.1 wherein a signal is used for activating an operational mode.

233.15 Standby signal:

Subject matter under subclass 233.1 wherein a clock signal is used for initiating a pause or power down mode.

233.16 Write mode signal only:

Subject matter under subclass 233.1 wherein a clock signal is used to control or start a write operation only.

233.17 Read mode signal only:

Subject matter under subclass 233.1 wherein a clock signal is used to control or start a read operation only.

233.18 Burst mode signal:

Subject matter under subclass 233.1 wherein a clock signal is used for transferring a group of data.

233.19 Common read and write mode signal:

Subject matter under subclass 233.1 wherein a clock signal is used to control or start both read and write operation.

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D. CHANGES TO THE DEFINITIONS

CLASS 369 – DYNAMIC INFORMATION STORAGE OR RETRIEVAL

Subclass 47.32: Under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, appropriate subclasses for a type of static memory, particularly subclasses 189.01 through 225.7 for read or write circuitry.

Insert:

365, Static Information Storage and Retrieval, appropriate subclasses for a type of static memory, particularly subclasses 189.011 through 225.7 for read or write circuitry.

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D. CHANGES TO THE DEFINITIONS

CLASS 370 – MULTIPLEX COMMUNICATIONS

Class Definition: Section II, under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclasses 189.01+ and 230.01+, for a static memory system with the handling of signal information or the addressing of memory locations respectively analogous to multiplexing techniques particularly subclasses 189.02 and 230.02 for such a system having multiplexed signals in each of the respective systems.

Insert:

365, Static Information Storage and Retrieval, subclasses 189.011 and 230.01+, for a static memory system with the handling of signal information or the addressing of memory locations respectively analogous to multiplexing techniques particularly subclasses 189.02 and 230.02 for such a system having multiplexed signals in each of the respective systems.

Subclass 395.7: Under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclasses 189.01 through 225.7 for read/write circuits in static information storage and retrieval.

Insert:

365, Static Information Storage and Retrieval, subclasses 189.011 through 225.7 for read/write circuits in static information storage and retrieval.

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D. CHANGES TO THE DEFINITIONS

CLASS 375 – PULSE OR DIGITAL COMMUNICATIONS

Class Definition: Section III, under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclasses 189.01+ and 230.01+ for a read/write or addressing circuit which uses pulse signals in a static storage system

Insert:

365, Static Information Storage and Retrieval, subclasses 189.011 and 230.01+ for a read/write or addressing circuit which uses pulse signals in a static storage system

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D. CHANGES TO THE DEFINITIONSCLASS 711 – ELECTRICAL COMPUTERS AND DIGITAL PROCESSING
SYSTEMS:MEMORY

Class Definition: Section II, under SEE OR SEARCH CLASS

Delete:

- 365, Static Information Storage and Retrieval, various subclasses for static memory devices including internal elements of the memory, particularly subclasses 189.01+ for read/write circuits and subclasses 230.01+ for addressing of addressable, static single storage elements or plural elements; subclass 189.05 for buffering or latching data being read from or written to memory; subclass 189.08 for logic devices in combination with memory systems; subclasses 200 and 201 for testing of memory systems; and subclass 230.08 for buffering and latching address data being employed to access memory.

Insert:

- 365, Static Information Storage and Retrieval, various subclasses for static memory devices including internal elements of the memory, particularly subclasses 189.011 for read/write circuits and subclasses 230.01+ for addressing of addressable, static single storage elements or plural elements; subclass 189.05 for buffering or latching data being read from or written to memory; subclass 189.08 for logic devices in combination with memory systems; subclasses 200 and 201 for testing of memory systems; and subclass 230.08 for buffering and latching address data being employed to access memory.

Subclass 1: Under SEE OR SEARCH CLASS

Delete:

- 365, Static Information Storage and Retrieval, subclasses 189.01+ for read/write circuits, and subclasses 230.01+ for addressing of addressable, static single storage elements or plural elements of the same type.

Insert:

- 365, Static Information Storage and Retrieval, subclasses 189.011 for read/write circuits, and subclasses 230.01+ for addressing of addressable, static single storage elements or plural elements of the same type.

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D. CHANGES TO THE DEFINITIONS

Subclass 3: Under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclasses 49+ for internal aspects of associative memory.

Insert:

365, Static Information Storage and Retrieval, subclasses 49.1 for internal aspects of associative memory.

Subclass 102: Under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, appropriate subclasses for storage having a particular internal cell structure (e.g., subclass 94 for read only (i.e., semipermanent) systems), subclasses 189.01+ for memory read/write circuits, and subclasses 230.01+ for addressing circuits

Insert:

365, Static Information Storage and Retrieval, appropriate subclasses for storage having a particular internal cell structure (e.g., subclass 94 for read only (i.e., semipermanent) systems), subclasses 189.011 for memory read/write circuits, and subclasses 230.01+ for addressing circuits

Subclass 108: Under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclasses 49 and 50 for associative memories or content addressable memories (CAM), per se.

Insert:

365, Static Information Storage and Retrieval, subclasses 49.1 through 50 for associative memories or content addressable memories (CAM), per se.

Subclass 113: Under SEE OR SEARCH CLASS

Delete:

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D. CHANGES TO THE DEFINITIONS

365, Static Information Storage and Retrieval, subclasses 49 and 50 for associative memories and caches under their class definition.

Insert:

365, Static Information Storage and Retrieval, subclasses 49.1 through 50 for associative memories and caches under their class definition.

Subclass 118: Under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclasses 49 and 50 for associative memories and caches at the cell level.

Insert:

365, Static Information Storage and Retrieval, subclasses 49.1 through 50 for associative memories and caches at the cell level.

Subclass 128: Under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclasses 49+ for associative memories or content addressable memories (CAM), per se.

Insert:

365, Static Information Storage and Retrieval, subclasses 49.1 through 50 for associative memories or content addressable memories (CAM), per se.

Subclass 200: Under SEE OR SEARCH CLASS

Delete:

365, Static Information Storage and Retrieval, subclasses 189.01+ for read/write circuits and subclasses 230.01+ for addressing of addressable, static single storage elements or plural elements of the same type.

Insert:

365, Static Information Storage and Retrieval, subclasses 189.011 for read/write circuits and subclasses 230.01+ for addressing of

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addressable, static single storage elements or plural elements of the same type.